Phase-Frequency Detector, 3.3 V, ECL

Description

The MC100EP140 is a three state phase frequency-detector intended for phase-locked loop applications which require a minimum amount of phase and frequency difference at lock. Since the part is designed with fully differential internal gates, the noise is reduced throughout the circuit, especially at high speeds. The basic operation of a Phase/Frequency Detector (PFD) is to "compare" an incoming signal (feedback) to a set reference signal. When the Reference (R) and Feedback (FB) inputs are unequal in frequency and/or phase, the differential UP (U) and DOWN (D) outputs will provide pulse streams which, when subtracted and integrated, provide an error voltage for control of a VCO. Detector states of operation are shown in the Figure 2 and the State Table.

The typical output amplitude of the EP140 is 400 mV, allowing faster switching time and greater bandwidth. For proper operation, the input edge rate of the R and FB inputs should be less than 5 ns.

More information on Phase Lock Loop operation and application can be found in AND8040.

The pinout is shown in Figure 1, the logic diagram in Figure 3, and the typical termination in Figure 5.

Features

- 500 ps Typical Propagation Delay
- Maximum Frequency > 2.1 GHz Typical
- Fully Differential Internally
- Advanced High Band Output Swing of 400 mV
- Transfer Gain: 1.0 mV/Degree at 1.4 GHz
 - 1.2 mV/Degree at 1.0 GHz
- Rise and Fall Time: 100 ps Typical
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.6 V with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = -3.0 V to -3.6 V
- Open Input Default State
- Pb-Free Packages are Available



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS*



SOIC-8 D SUFFIX CASE 751



A = Assembly Location

L = Wafer Lot
 Y = Year
 W = Work Week

= Pb-Free Package

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

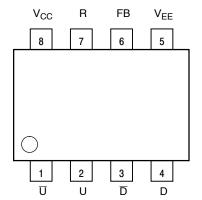


Figure 1. 8-Lead Pinout (Top View)

Table 1. PIN DESCRIPTION

PIN	FUNCTION		
D, \overline{D}	Differential Down Outputs		
U, U Differential Up Outputs			
R* ECL Reference Input			
FB*	ECL Feedback Input		
V _{CC} Positive Supply			
V _{EE}	Negative Supply		

^{*} Pins will default LOW when left open.

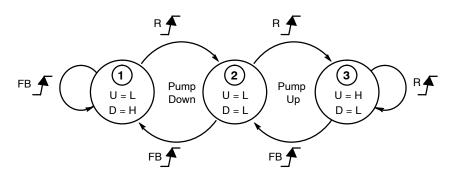


Figure 2. Phase Detector Logic Model

Table 2. STATE TABLE

PHASE DETECTOR	INF	PUT	OUT	PUT
STATE	R	FB	U	D
PUMP DOWN 2-1-2				
2	L	L	L	L
2–1	L	Н	L	Н
1–2	Н	L	L	L
2	L	L	L	L
PUMP UP 2-3-2				
2	L	L	L	L
2–3	Н	L	н	L
3–2	Н	Н	L	L
2	L	L	L	L

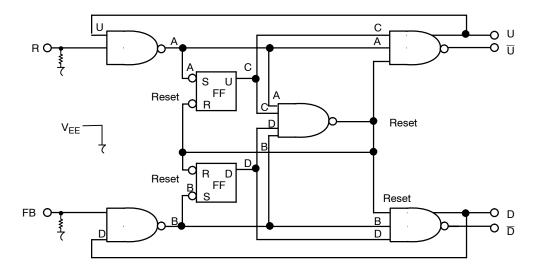


Figure 3. Logic Diagram

Table 3. ATTRIBUTES

Characteristic	Va	lue				
Internal Input Pulldown Resistor	75 kΩ					
Internal Input Pullup Resistor	37.5	5 kΩ				
ESD Protection	> 2 > 20 > 2					
Moisture Sensitivity, Indefinite Time (Out of Drypack (Note 1)	Pb Pkg	Pb-Free Pkg			
	SOIC-8	Level 1	Level 1			
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0	@ 0.125 in			
Transistor Count	457 D	evices				
Meets or exceeds JEDEC Spec EIA/	Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test					

^{1.} For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V _{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
V _I	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$V_{I} \leq V_{CC}$ $V_{I} \geq V_{EE}$	6 -6	V V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			−65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 SOIC-8	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44	°C/W
T _{sol}	Wave Solder Pb Pb-Free			265 265	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 5. 100EP DC CHARACTERISTICS, PECL V_{CC} = 3.3 V, V_{EE} = 0 V (Note 2)

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	45	65	85	50	70	90	53	73	93	mA
V _{OH}	Output HIGH Voltage (Note 3)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 3)	1755	1880	2005	1755	1880	2005	1755	1880	2005	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 2. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -0.3 V.
- 3. All loading with 50 Ω to V_{CC} 2.0 V.

Table 6. 100EP DC CHARACTERISTICS, NECL $V_{CC} = 0 \text{ V}$, $V_{FF} = -3.6 \text{ V}$ to -3.0 V (Note 4)

		−40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	45	65	85	50	70	90	53	73	93	mA
V _{OH}	Output HIGH Voltage (Note 5)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 5)	-1545	-1420	-1295	-1545	-1420	-1295	-1545	-1420	-1295	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 4. Input and output parameters vary 1:1 with V_{CC}.
- 5. All loading with 50 Ω to V_{CC} 2.0 V.

Table 7. AC CHARACTERISTICS $V_{CC} = 0 \text{ V}$; $V_{EE} = -3.0 \text{ V}$ to -3.6 V or $V_{CC} = 3.0 \text{ V}$ to 3.6 V; $V_{EE} = 0 \text{ V}$ (Note 6)

				-40°C			25°C			85°C		
Symbol	Characteris	stic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency (Fig	ure 4)		> 2			> 2			> 2		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential	R to U, FB to D FB to U, R to D	300 400	450 600	6002 800	325 450	475 650	625 850	350 500	500 700	650 900	ps
t _{JITTER}	Cycle-to-Cycle Jitter (Figure 4)			.2	< 1		.2	< 1		.2	< 1	ps
V_{PP}	Input Voltage Swing		400	800	1200	400	800	1200	400	800	1200	mV
t _r t _f	Output Rise/Fall Times (20% - 80%)	Q, \overline{Q}	50	90	180	60	100	200	70	120	220	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

6. Measured using a 750 mV V_{PP} pk-pk, 50% duty cycle, clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

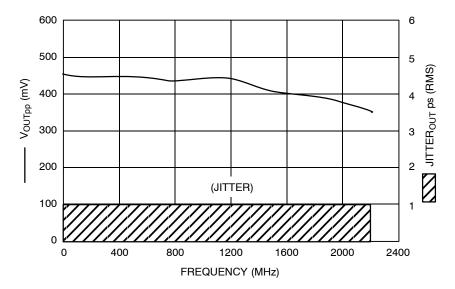


Figure 4. F_{max}/Jitter

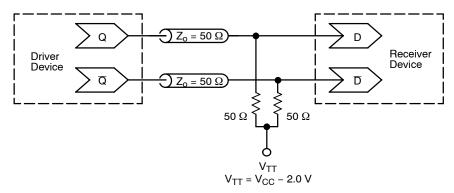


Figure 5. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100EP140D	SOIC-8	98 Units / Rail
MC100EP140DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC100EP140DR2	SOIC-8	2500 / Tape & Reel
MC100EP140DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D - The ECL Translator Guide

AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

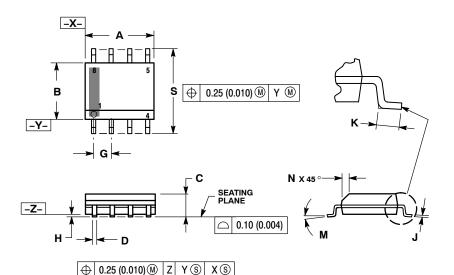
AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices



SOIC-8 NB CASE 751-07 **ISSUE AK**

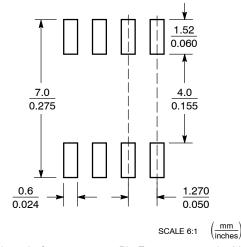
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.33 0.51		0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
M	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week = Pb-Free Package XXXXXX AYWW AYWW Ŧ \mathbb{H} Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DHAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	0 COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

DOCUMENT NUMBER:	98ASB42564B	Printed versions are uncontrolled except when stamped "CONTROLLED	' '
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative